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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number		Filed Herewith				
		Filing Date		July 16, 2003				
		First Named Inventor:		Aaditya Mahajan				
		Examiner name: unknown		GROUP: unknown				
Sheet	1	of	1	Attorney Docket Number		TRQ-12957		
U.S. PUBLISHED PATENT APPLICATIONS								
Examiner Initials*	Cited No. ¹	U.S. Patent Document Number Kind Code ² (if known)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear	
U.S. PATENT DOCUMENTS								
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FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cited No. ¹	Foreign Patent Document Office ³ Number ⁴ Kind Code ⁵ (if known)		Name of Patentee or Applicant of Cited Document		Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear	T ⁶
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
PL	Bollaert et al., "Metamorphic In _{0.4} Al _{0.6} As/In _{0.4} Ga _{0.6} As HEMT's on GaAs Substrate", IEEE Electron Device Letters, Vol. 20, No. 3, March 1999, pp. 123-125.							
PL	Dumka et al., "High Performance 0.35 μm Gate-Length Monolithic Enhancement/Depletion-Mode Metamorphic In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As HEMTs on GaAs Substrates", IEEE Electron Device Letters, Vol. 22, No. 8, August 2001, pp. 364-366.							
PL	Hoke et al., "Molecular Beam Epitaxial Growth And Device Performance Of Metamorphic High Electron Mobility Transistor Structures", J. Vac. Sci. Technol. B, Vol. 17, No. 3, May/Jun 1999, pp. 1131-1135.							
PL	Jang et al., "Long Wavelength Metamorphic Double Heterojunction In _{0.53} Ga _{0.47} As/InAlGaAs/In _{0.52} Al _{0.48} As Photodiodes On GaAs Substrates", Electronics Letters, Vol. 37, No. 11, May 24, 2001.							
PL	Jang et al., "The Impact Of A Large Bandgap Drift Region In Long-Wavelength Metamorphic Photodiodes", IEEE Photonics Technology letters, Vol. 13, No. 10, October 2001, pp. 1097-1099.							
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PL	Zaknour et al., "InAlAs/InGaAs Metamorphic HEMT With High Current Density And High Breakdown Voltage", IEEE Electron Device Letters, vol. 19, No. 9, September 1998, pp. 345-347.							
EXAMINER		DATE CONSIDERED		1/5/2005				

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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